



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant

: Chang-Rong WU et al.

Confirmation No: 9777

Appl. No.

: 10/810,804

Filed

: March 29, 2004

Title

: Method And Composite Hard Mask For Forming Deep

Trenches In A Semiconductor Substrate

TC/A.U.

: 2823

Examiner

: F.L. Toledo

Docket No.:

: WUCH3037/REF

Customer No:

: 23364

AMENDMENT

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of March 9, 2006, in connection with the above-identified application. This response is timely filed.

Please amend the application as follows:

Amendments to the claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks begin on page 4 of this paper.